

## IGBT (NPT) Module

$$V_{CES} = 1200V$$

$$I_{C25} = 135A$$

$$V_{CE(sat)} = 2.2V$$


Boost Chopper + free wheeling Diode

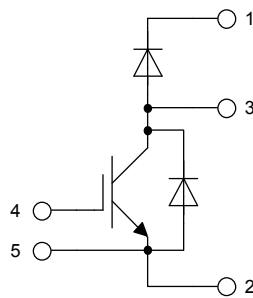
Part number

MID100-12A3



Backside: isolated

 E72873



### Features / Advantages:

- NPT IGBT technology
- low saturation voltage
- low switching losses
- switching frequency up to 30 kHz
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy parallelling
- MOS input, voltage controlled
- ultra fast free wheeling diodes

### Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

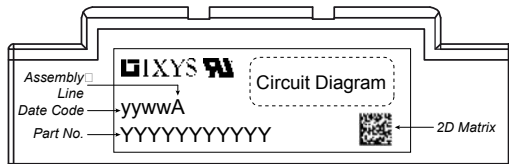
### Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Free Wheeling Diode FWD				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
$V_{RRM}$	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
$I_R$	reverse current, drain current	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		1	mA
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$		3	mA
$V_F$	forward voltage drop	$I_F = 75 A$	$T_{VJ} = 25^{\circ}C$		2.50	V
					2.90	V
		$I_F = 150 A$	$T_{VJ} = 125^{\circ}C$		1.80	V
					2.10	V
$I_{FAV}$	average forward current	$T_C = 80^{\circ}C$ DC current $d = 1$	$T_{VJ} = 150^{\circ}C$		75	A
$V_{FO}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.30	V
$r_F$	slope resistance				7.5	mΩ
$R_{thJC}$	thermal resistance junction to case				0.45	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.45		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$		280	W
$I_{FSM}$	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		700	A
$C_J$	junction capacitance	$V_R = 600 V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		30	pF

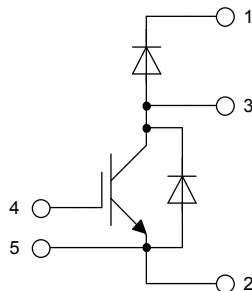
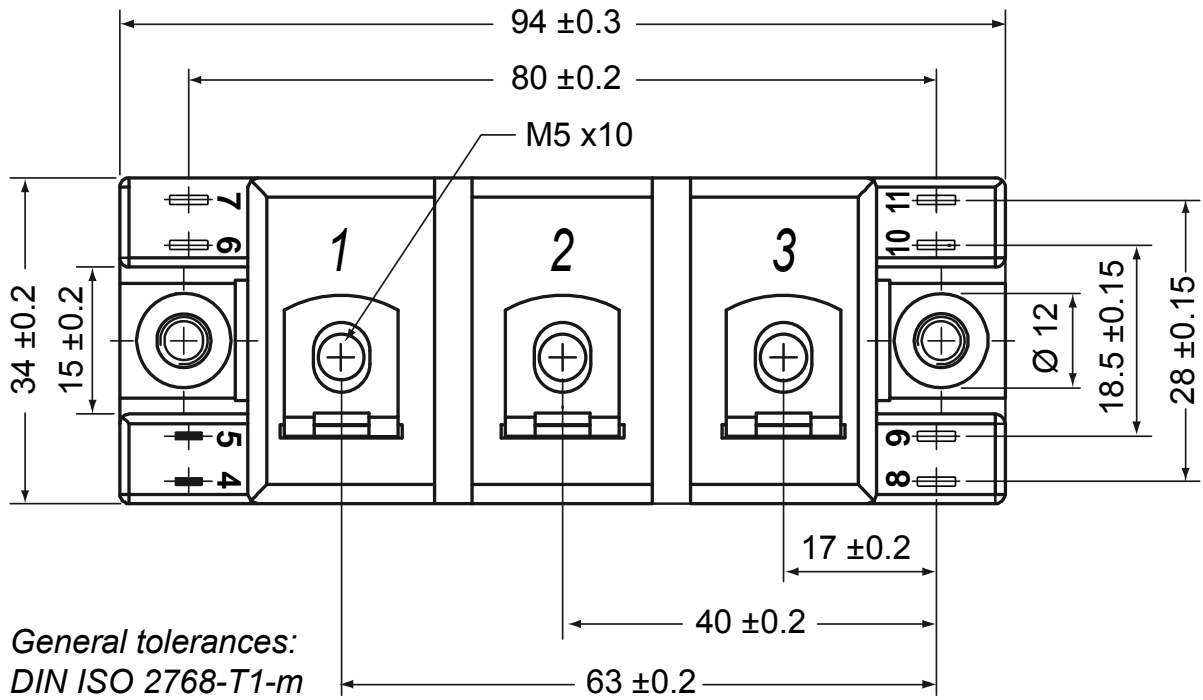
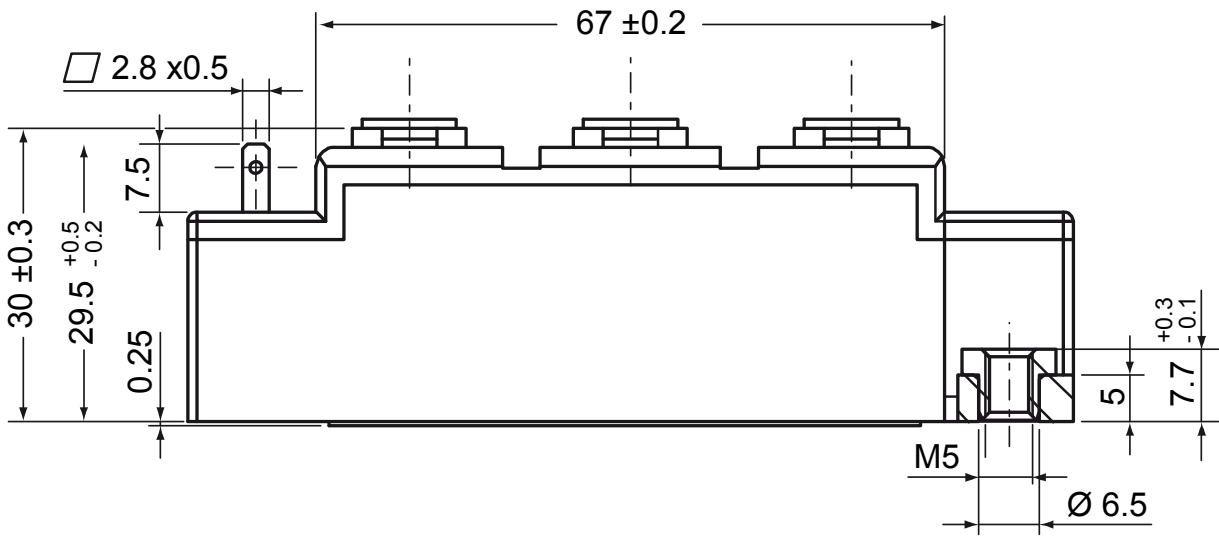
<b>Boost IGBT</b>				<b>Ratings</b>			
<b>Symbol</b>	<b>Definition</b>	<b>Conditions</b>	<b>min.</b>	<b>typ.</b>	<b>max.</b>	<b>Unit</b>	
$V_{CES}$	collector emitter voltage				1200	V	
$V_{GES}$	max. DC gate voltage				±20	V	
$V_{GEM}$	max. transient gate emitter voltage				±30	V	
$I_{C25}$	collector current				135	A	
$I_{C80}$					90	A	
$P_{tot}$	total power dissipation				560	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 75A; V_{GE} = 15V$			2.2	V	
					2.7	V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 3mA; V_{GE} = V_{CE}$	4.5	5.5	6.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0V$			5	mA	
					7.5	mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20V$			300	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600V; V_{GE} = 15V; I_C = 75A$		350		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600V; I_C = 75A$ $V_{GE} = \pm 15V; R_G = 15\Omega$		100		ns	
$t_r$	current rise time			50		ns	
$t_{d(off)}$	turn-off delay time			650		ns	
$t_f$	current fall time			50		ns	
$E_{on}$	turn-on energy per pulse			12.1		mJ	
$E_{off}$	turn-off energy per pulse			10.5		mJ	
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15V; R_G = 15\Omega$					
$I_{CM}$		$V_{CEmax} = 1200V$			150	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEmax} = 1200V$					
$t_{sc}$	short circuit duration	$V_{CE} = 1200V; V_{GE} = \pm 15V$			10	µs	
$I_{sc}$	short circuit current	$R_G = 15\Omega; \text{non-repetitive}$		270		A	
$R_{thJC}$	thermal resistance junction to case				0.22	K/W	
$R_{thCH}$	thermal resistance case to heatsink				0.22	K/W	
<b>Boost Diode BD</b>							
$V_{RRM}$	max. repetitive reverse voltage				1200	V	
$I_{F25}$	forward current				150	A	
$I_{F80}$					95	A	
$V_F$	forward voltage	$I_F = 75A$			2.50	V	
					1.70	V	
$I_R$	reverse current	$V_R = V_{RRM}$			1	mA	
					1.5	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 600V$ $-di_F/dt = 600A/\mu s$ $I_F = 75A; V_{GE} = 0V$		7		µC	
$I_{RM}$	max. reverse recovery current			62		A	
$t_{rr}$	reverse recovery time			200		ns	
$E_{rec}$	reverse recovery energy			1.2		mJ	
$R_{thJC}$	thermal resistance junction to case				0.45	K/W	
$R_{thCH}$	thermal resistance case to heatsink				0.45	K/W	

Package Y4				Ratings		
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			300	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>					108	g
$M_D$	mounting torque		2.25		2.75	Nm
$M_T$	terminal torque		4.5		5.5	Nm
$d_{Sppl/App}$	creepage distance on surface   striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm
$V_{ISOL}$	isolation voltage	t = 1 second			3600	V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000	V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MID100-12A3	MID100-12A3	Box	6	466816

## Outlines Y4



## Boost IGBT

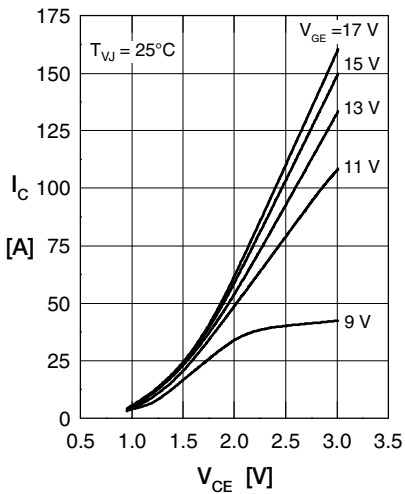


Fig. 1 Typ. output characteristics

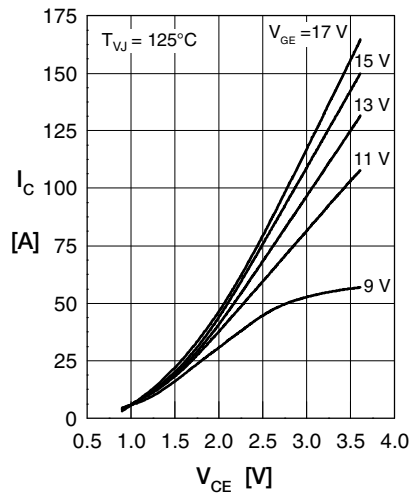


Fig. 2 Typ. output characteristics

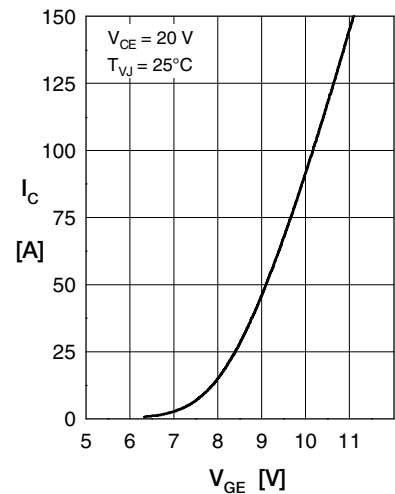


Fig. 3 Typ. transfer characteristics

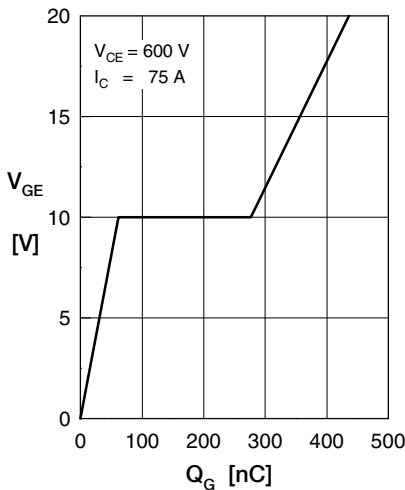


Fig. 4 Typ. turn-on gate charge

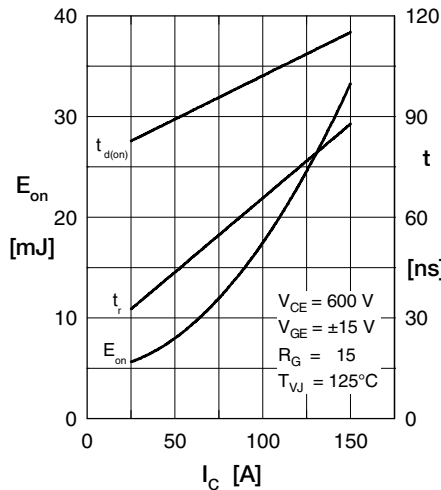


Fig. 5 Typ. turn on energy & switching times versus collector current

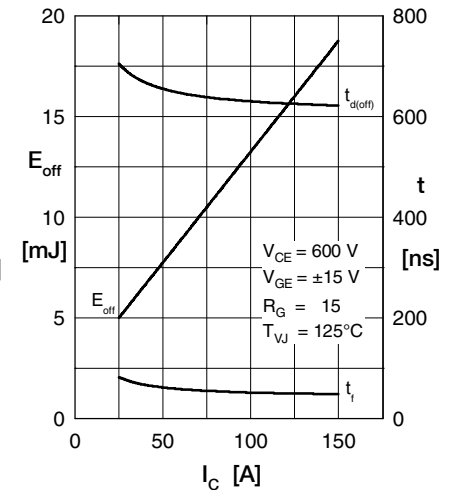


Fig. 6 Typ. turn off energy & switching times versus collector current

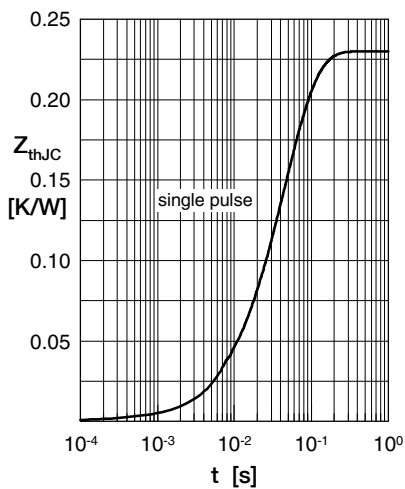


Fig. 12 Typical transient thermal impedance

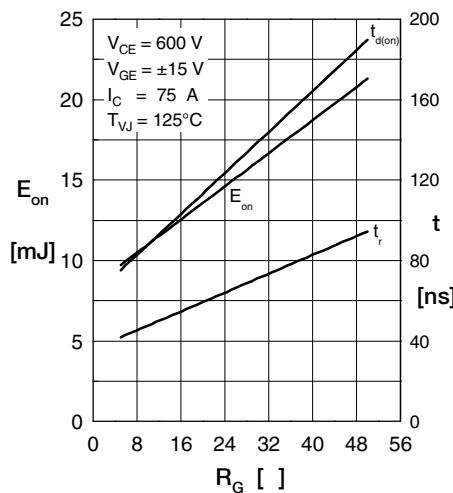


Fig. 9 Typ. turn on energy & switching times versus gate resistor

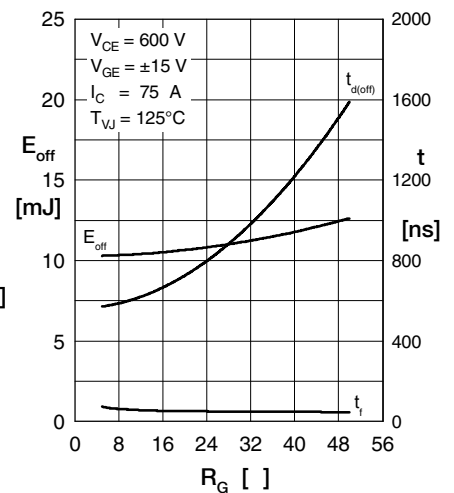


Fig. 9 Typ. turn off energy & switching times versus gate resistor

**Boost Diode BD**

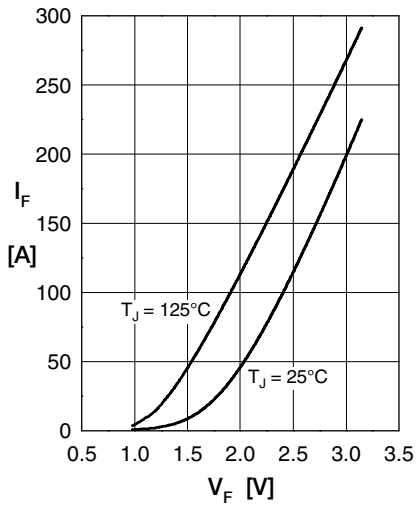


Fig. 1 Typ. Forward current vs.  $V_F$

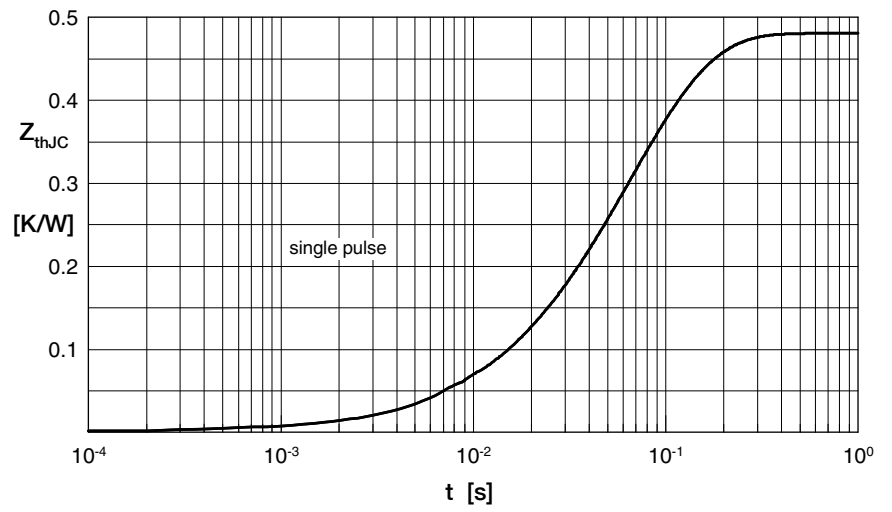


Fig. 2 Typ. transient thermal impedance junction to case